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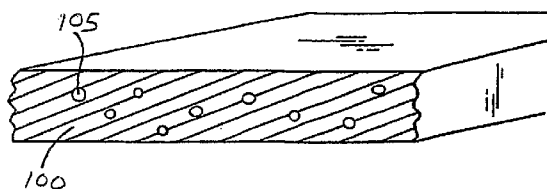
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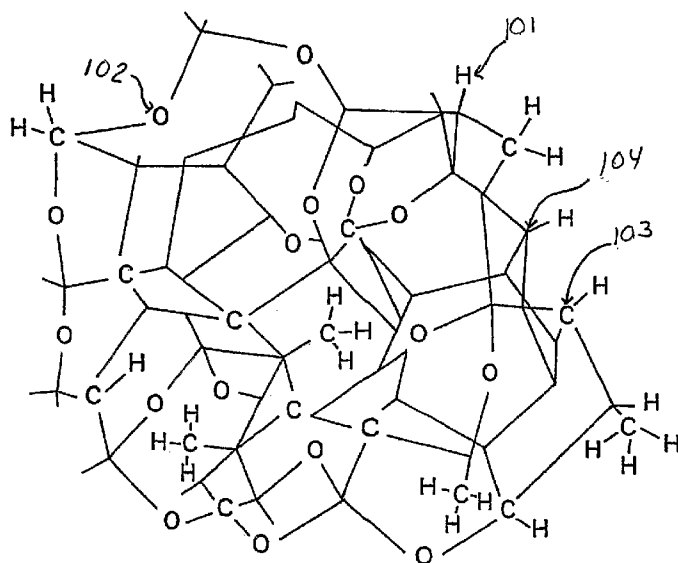
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(54) Title: **ULTRA LOW K (ULK) SICOH FILM AND METHOD**



A



B

(57) Abstract: The present invention provides a multiphase, ultra low k film which exhibits improved elastic modulus and hardness as well as various methods for forming the same. The multiphase, ultra low k dielectric film includes atoms of Si, C, O and H, has a dielectric constant of about 2.4 or less, nanosized pores or voids, an elastic modulus of about 5 or greater and a hardness of about 0.7 or greater. A preferred multiphase, ultra low k dielectric film includes atoms of Si, C, O and H, has a dielectric constant of about 2.2 or less, nanosized pores or voids, an elastic modulus of about 3 or greater and a hardness of about 0.3 or greater.



GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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- *as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii)) for all designations*

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